



### 65V DUAL NPN SMALL SIGNAL TRANSISTOR

## Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

### **Features**

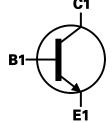
- BV<sub>CEO</sub> > 65V
- I<sub>C</sub> = 100mA High Collector Current
- Complementary PNP Types Available (BC856ASQ)
- Ideally Suited for Automatic Insertion
- For Switching and AF Amplifier Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

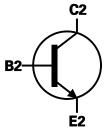
## **Mechanical Data**

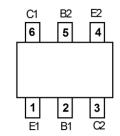
- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Finish. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)

### **SOT363**









Device Symbol

Top View Pin-Out

## Ordering Information (Notes 4 and 5)

Top View

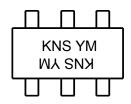
Ī	Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
	BC846ASQ-7-F	Automotive	KNS	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/product-compliance-definitions/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

## **Marking Information**

### **SOT363**



KNS = Product Type Marking Code YM = Date Code Marking Y = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

Year	2016 2017 2018			2019	2020		2021	2022		2023		
Code	D		E	F		G	Н		ı	J		K
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



## Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	80	V
Collector-Emitter Voltage	$V_{CEO}$	65	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current	Ic	100	mA
Peak Collector Current	I <sub>CM</sub>	200	mA
Peak Emitter Current	I <sub>EM</sub>	200	mA

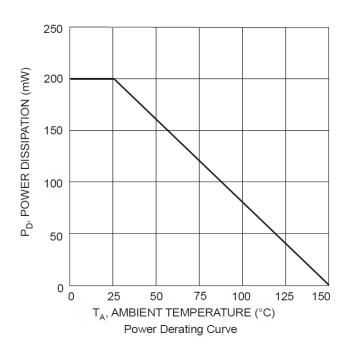
# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	$P_{D}$	200	mW
Thermal Resistance, Junction to Ambient Air (Note 6)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	٧	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 6. For a device mounted on minimum recommended pad layout FR-4 PCB with high coverage of single sided 1oz copper; device is measured under still air conditions whilst operating in a steady-state.
7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.





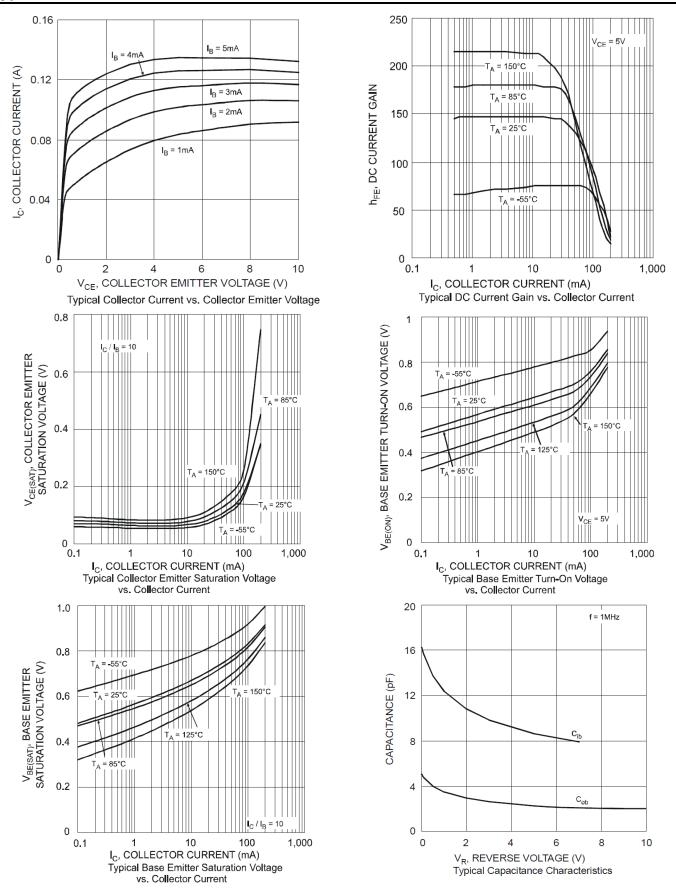
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic (Note 8)	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	80		_	V	$I_C = 10\mu A$
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	65	1		<b>V</b>	$I_C = 10mA$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	6	-	-	V	$I_E = 1\mu A$
DC Current Gain	h <sub>FE</sub>	110		220		$V_{CE} = 5.0V, I_{C} = 2.0mA$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>		90 200	250 600	mV	$I_C = 10mA, I_B = 0.5mA$ $I_C = 100mA, I_B = 5.0mA$
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>		700 900		mV	$I_C = 10mA, I_B = 0.5mA$ $I_C = 100mA, I_B = 5.0mA$
Base-Emitter Voltage	V <sub>BE(ON)</sub>	580 —	660 —	700 770	mV	$V_{CE} = 5.0V, I_{C} = 2.0mA$ $V_{CE} = 5.0V, I_{C} = 10mA$
Collector-Cutoff Current	ICES ICBO ICBO	111	111	15 15 5.0	nΑ nA μΑ	V <sub>CB</sub> = 80V V <sub>CB</sub> = 40V V <sub>CB</sub> = 30V, T <sub>A</sub> = +150°C
Gain Bandwidth Product	f <sub>T</sub>	100			MHz	V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 10mA, f = 100MHz
Collector-Base Capacitance	C <sub>CB</sub>	_	2	_	pF	V <sub>CB</sub> = 10V, f = 1.0MHz

Note: 8. For Short duration pulse test used to minimize self-heating effect.

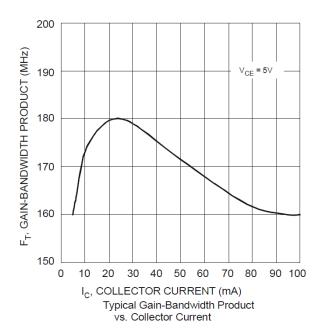


## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)





## Typical Electrical Characteristics (Cont. @TA = +25°C, unless otherwise specified.)

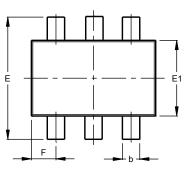


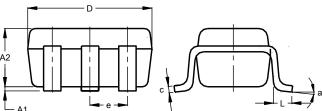


## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### **SOT363**



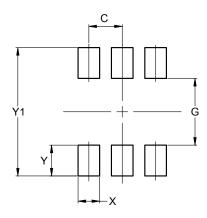


SOT363							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	1.00				
b	0.10	0.30	0.25				
С	0.10	0.22	0.11				
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	(	).650 E	SC				
F	0.40	0.45	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All Dimensions in mm							

# **Suggested Pad Layout**

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html for the latest version.$ 

### **SOT363**



Dimensions	Value			
Dilliensions	(in mm)			
С	0.650			
G	1.300			
Х	0.420			
Y	0.600			
Y1	2.500			

October 2017

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